

Reliability Report: DS1808

Process: 1P, 1M, 5.0um, 30V NF & PF, UVNd, UVPd ,N+ESD,TEOS Spacer, Passivation w/Nov TEOS Oxide-Nitride

Metal: Al / 0.5% Cu / 0.8% Si Gate Ox Thickness: 225 Å Pin Count: 16

Summary Data with Chi-Square Distribution Assumed. Stress Ambient Temperature and Voltage to Field Ambient Temperature And Voltage	Cf: 60%	Tuse: 25 °C	Assembly: ATP (Amkor, PI)
	Ea: 0.7	Vuse: 5.5 Volts	Package: SOIC
	β: 0		Body Size: 150x1.4

DESCRIPTION	VEHICLE	REV	DATE CODE	CONDITION	READPOINT	QUANTITY	FAILS	FILE #	DEVICE HRS
HIGH TEMPERATURE OPERATING LIFE									
HIGH VOLTAGE LIFE	DS1808	A2	0133	125C, 6.0 V (PSA) & +13.2 V (PS	6	HOURS	80	0	452720
	DS1808	A2	0133	125C, 6.0 V (PSA) & +13.2 V (PS	336	HOURS	80	0	24899612
				DEVICE HRS: 2.54E+07		TOTALS:	0		
				FAILURE RATE	MTBF (yrs): 3158	FITS:	36		

<u>PRODUCT</u>	<u>REV</u>	<u>DIE SIZE (x)</u>	<u>DIE SIZE (y)</u>	<u>No. of Transistors</u>
DS1808	A2	159	80	1700